

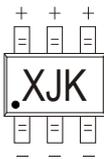
## Plastic-Encapsulate Diodes

### SWITCHING DIODE

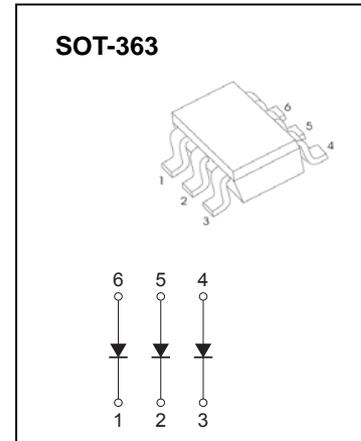
#### FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

#### MARKING:



Solid dot = Pin1 indicate.



### MAXIMUM RATINGS ( $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak repetitive peak reverse voltage	$V_{RRM}$	250	V
Working peak reverse voltage	$V_{RWM}$	250	V
DC blocking voltage	$V_R$	250	V
Forward continuous current	$I_{FM}$	400	mA
Average rectified output current	$I_O$	200	mA
Non-repetitive peak forward surge current @ $t = 8.3\text{ms}$	$I_{FSM}$	2.5	A
Repetitive peak forward surge current	$I_{FRM}$	625	mA
Power dissipation	$P_D$	225	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	555	$^\circ\text{C}/\text{W}$
Operating junction and storage temperature range	$T_j, T_{stg}$	-55 ~ 150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{BR}$	$I_R = 100\mu\text{A}$	250	-	-	V
Forward voltage	$V_{F1}$	$I_F = 100\text{mA}$	-	-	1	V
	$V_{F2}$	$I_F = 200\text{mA}$	-	-	1.25	
Reverse current	$I_R$	$V_R = 200\text{V}$	-	-	0.1	$\mu\text{A}$
Capacitance between terminals	$C_T$	$V_R = 0\text{V}, f = 1\text{MHz}$	-	-	5	pF
Reverse recovery time	$t_{rr}$	$I_F = I_R = 30\text{mA}, I_{rr} = 3\text{mA}, R_L = 100\Omega$	-	-	50	ns

## Typical Characteristics

